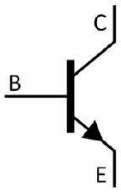
VRW0;< ṂṂ Ḅ QSQ ÆṀ ч s Ⅱ ㄱ Silicon NPN transistor in a SOT-89 Plastic Package.

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Low $V_{CE(sat)}$, high current, HF Product.

₹ ˇ ˉ ˍ Ầ ԋ ı ὺ Ǐ ~ ʜ [OBJ] ὖ ˇ Ł ˝ ı ㅓ ớ Ầ ԋ Ɔ ◊

General purpose switching and muting, LCD back-lighting, supply line switching circuits.

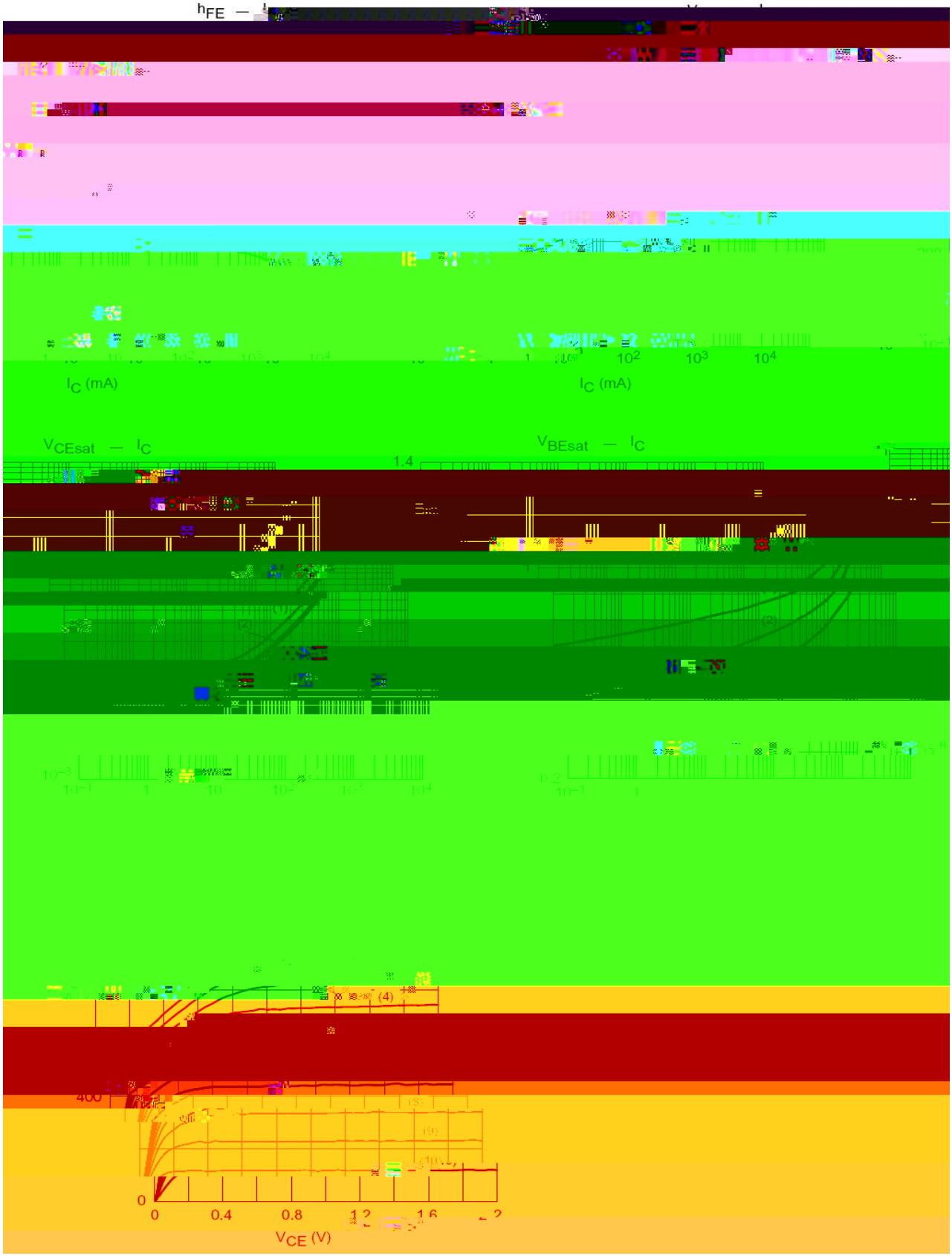


v ̈Ω Parameter	ϒ N Symbol	̈Ω Ö Rating	D Ч Unit
Collector to Base Voltage	V_{CBO}	50	V
Collector to Emitter Voltage	V_{CEO}	50	V
Emitter to Base Voltage	V_{EBO}	5	V
Collector Current - Continuous	I_C	3	A
Collector Base - Continuous	I_B	0.5	A
Peak Collector Current	I_{CM}	5	A
Total Power Dissipation	P_{tot} ϔ 4	550	mW
Junction Temperature	T_j	150	
Storage Temperature Range	T_{stg}	-65 150	

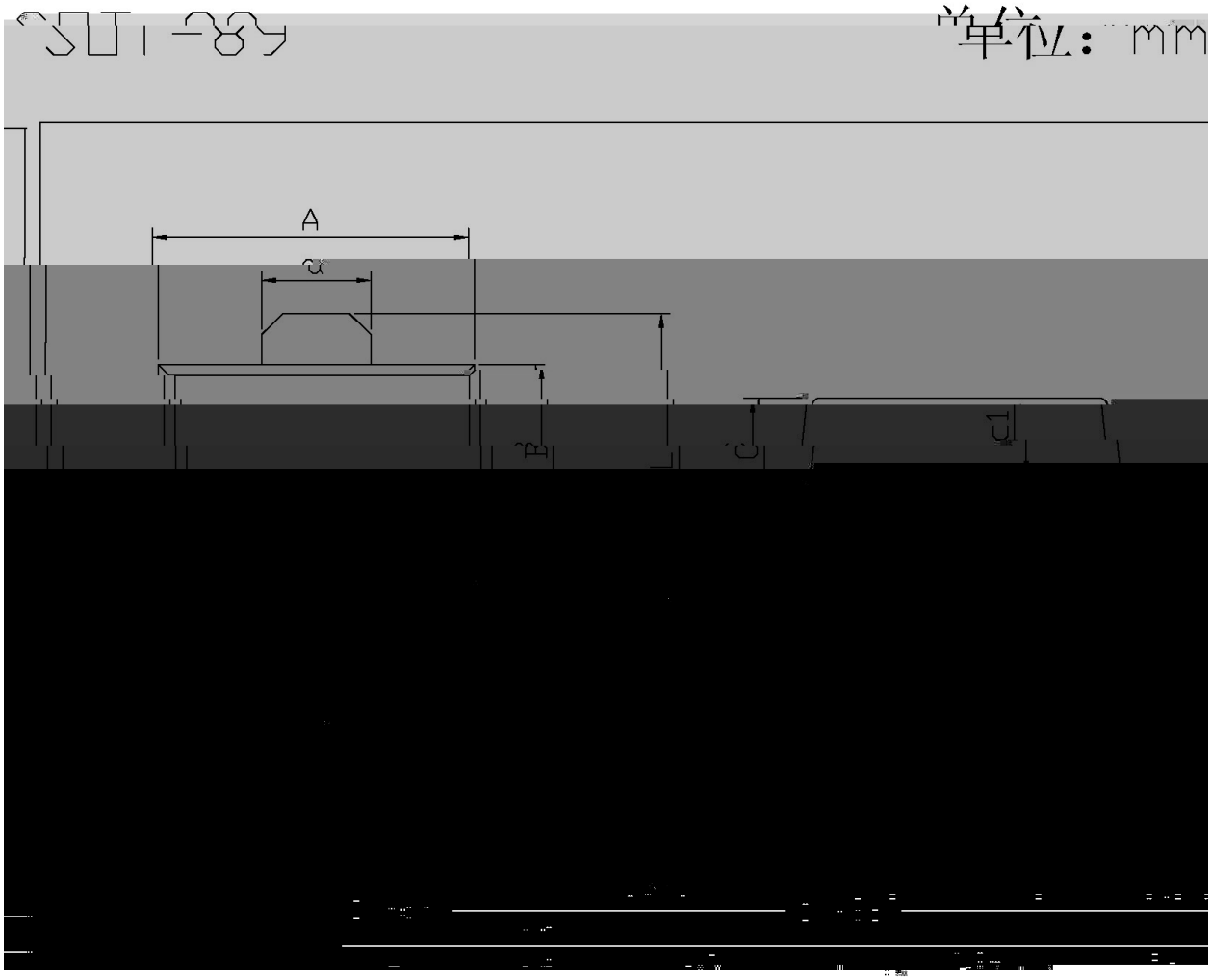
4 λ ϶ ϯ Ḡ Ł ϱ м ͅ Ɔ ب — i

v ̈Ω Parameter	ϒ N Symbol	Ш ː ϯ ϯ Test Conditions	ω ṇ Ö Min	Ɛ ʒ Ö Typ	ω ᶻ Ö Max	D Ч Unit
Collector Cut-Off Current	I_{CBO}	V_{CB}=50V I_E=0			100	nA
Collector Cut-Off Current	I_{CBO}	V_{CB}=50V I_E=0 T_j=150			50	A
Collector Cut-Off Current	I_{CES}	V_{CE}=50V V_{BE}=0			100	nA
Emitter Base Cut-Off Current	I_{EBO}	V_{EB}=5.0V I_C=0			100	nA
DC Current Gain	$h_{FE(1)}$	V_{CE}=2.0V I_C=0.1A	300			
	$h_{FE(2)}$	V_{CE}=2.0V I_C=0.5A	300			
	$h_{FE(3)*}$	V_{CE}=2.0V I_C=1.0A	300		700	

/ Electrical Characteristic Curve



/ Package Dimensions



PBSS4350X

Rev.G Jul.-2025

( ) /

ب ˝ χ

1 Ĺ ♬ □ ỷ 150 Ḱ 180 ł ı `H ڑ 60 Ḱ 90sec;

2 Š Ө □ ỷ 245 ° 5 ł ı `H ڑ `Y ㅅ ㎞ 5 ° 0.5sec;

3 ì ˙ ㅓ ˛ ɔ ෯ ỷ ㎞ 2 Ḱ 10 ł /sec.

Note:

1.Preheating:150~180 ł , Time:60~90sec.

2.Peak Temp.:245 ° 5 ł , Duration:5 ° 0.5sec.

3. Cooling Speed: 2~10 ł /sec.

/ Resistance to Soldering Heat Test Conditions

□ ỷ χ 260 ° 5 ł	`H ڑ χ 10 ° 1 sec.	Temp.:260±5	Time:10±1 sec

/ Packaging SPEC.

ი ` ㅓ Ь / REEL

Package Type	Units	Dimension	(unit mm³)